AN8032 Active-Filter Control IC

Overview

When the power is supplied from the commercial power supply to the electrical equipment, the harmonic distortion generating in the power line may give obstruction to the power facilities or other electrical equipments.

The active filter is used to protect against such harmonic distortion problems.

The AN8032 is a monosilic IC which incorporates the control functions and protection ones into one package so that the active filter can be easily constructed. So, it is suitable for the lighting equipments, which otherwise suffers from the harmonic distortion.

Features

- Automatic peak current mode employed
- Built-in circuit preventing the overvoltage generated under the small load
- Easy constant setting with enlarged dynamic range of multiplier/error amplifier.
- Overvoltage protection terminal separately set to pass the short test of the safety standards
- Employed totem pole output circuit which allows the power MOS-FET to be directly driven.
- Built-in low voltage protective circuit which ensures the ONresistance during the power MOS-FET operation.
- Built-in timer circuit which can realize the automatic start

Application

- Lighting equipment
- Switching power supply



Pin Assignments



Block Diagram



■ Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Rating	Unit
Supply voltage	Vcc	35	V
Output allowable current	Io	±150	mA
Peak output current	Іор	±1	А
VB allowable in-current	Іві	+5	mA
VB allowable out-current	Іво	-5	mA
VD allowable applied voltage	Vcs	– 0.5 to 7	V
MPI allowable applied voltage	VMPI	– 0.5 to 7	V
EI allowable applied voltage	VEI	– 0.5 to 7	V
Power dissipation	PD	874	mW
Operating ambient temperature	Topr	-30 to 85	°C
Storage temperature	T _{stg}	-55 to 150	°C

■ Recommended Operating Conditions (Ta=25°C)

Parameter	Symbol	min	max	Unit
Supply voltage	V _{CC}	0	34	V

■ Electrical Characteristics (Ta=25±2°C)

Parameter	Symbol	Condition	min	typ	max	Unit
Error detection feedback threshold voltage 1	V_{E1}^{TH1}		2.35	2.50	2.65	V
Error detection output L voltage	V _{EO} ^L	I _{EO} =0mA, V _{EI} =5V		1.0	1.6	V
Error detection output H voltage	V _{EO} ^H	I _{EO} =0mA, V _{EI} =0V	5.0	5.7		V
Error detection input bias current	I _{EI}	V _{EI} =0V		- 0.3	-1.0	μΑ
Error detection output supply current	I _{EO}	V _{EI} =0V, V _{EO} =1V	0.25	0.50	0.75	mA
Multiplier input D-range (upper limit)	V _{MPI} ^H	V _{EO} =5V	4.0	4.5		V
Multiplier output D-range (upper limit)	V _{MPO} ^H	V _{EO} =5V	4.8	5.4		V
Multiplier gain	G _{MP}		1.0	1.2	1.4	1/V
Multiplier input bias current	I _{MPI}	V _{MPI} =0V		-1.5	-3.0	μΑ
Winding detection input threshold voltage	V _B TH		1.2	1.5	1.8	V
Winding detection hysteresis width	dV _B		50	100	200	mV
Winding detection H clamp voltage	V _B ^H	I _B =5mA	7.0	7.5	8.0	v
Winding detection L clamp voltage	VBL	I _B =-5mA	- 0.3	- 0.2	0	v
Current detection input offset voltage	V _{CS} ^{OFF}			3.5	15	mV
Current detection input bias current	I _{CS}	V _{CS} =0V		- 0.5	-2.0	μΑ
Overvoltage detection input threshold voltage	V _{OVP}		2.45	2.60	2.75	V
$V_{OVP} - V_{EI}^{TH1}$	_		70	100	130	mV
Output L voltage	VOUTL	I _{OUT} =100mA		0.9	1.5	V
Output H voltage	V _{OUT} ^H	I _{OUT} =-100mA	9.2	10.2		V
Stand-by output voltage	VOUTSTB	I _{OUT} =10mA		0.8	1.5	v
UVLO start voltage	V _{CC} ST		9.2	10.0	10.8	V
UVLO stop voltage	V _{CC} ^{SP}		7.0	8.0	9.0	V
UVLO start-stop voltage difference	dV _{CC}	$dV_{CC} = V_{CC}^{ST} - V_{CC}^{SP}$	1.75	2.00	2.50	V
Stand-by current	I _{CC} ^{STB}	V _{CC} =7V	40	80	120	μΑ
No load operation current	I _{CC}	V _{CC} =12V		6.0	10.0	mA

Electrical Characteristics (for Design Reference)

Note) These values are design reference values, not guaranteed ones.

Parameter	Symbol	Condition	Reference value	Unit
Error detection feedback threshold voltage 2	$V_{\rm EI}{}^{\rm TH2}$	$Ta=-25^{\circ}C$ to $+85^{\circ}C$	2.3 to 2.7	V
Error detection open – loop gain	G _{AV}		85	dB
Error detection gain band width	\mathbf{f}_{BW}	V _{EO} =5V	1.0	MHz
Multiplier input D-range (lower limit)	V_{MPI}^{L}	V _{EO} =5V	0	V
Multiplier output D-range (lower limit)	V _{MPO} ^L		0	V
Current detection – output delay	td ^{CS}		200	nS
Overvoltage detection – output delay	td ^{ovp}	$V_{CC}=12V, V_{OUT}=10\rightarrow 90\%$	500	nS
Output rise time	tr	$V_{CC}=12V, V_{OUT}=90\rightarrow 10\%$	50	nS
Output fall time	tr		50	nS
Timer delay time	td ^{TIM}		400	μS

Power Dissipation



Pin No.	Pin name	I/O	Terminal description	Internal equivalent circuit
1	CS	Ι	Input terminal for comparator which detects the value of current flowing in power MOS FET. It compares the output level of multiplier and the current value of power MOS FET which is inputted from CS terminal. When the latter value gets larger than the former value, it sets VOUT "L" to shut off the power MOS FET.	CS (1)
2	MPI	I	Input terminal for multiplier It monitors the voltage after the AC input voltage is full-wave-recti- fied.	—7.1V
3	EO	0	Double function : Output terminal for error amp. and input terminal for multiplier. For error amp., it monitors the output voltage of active filter to amplify the error for output to mul- tiplier. It also functions as another input terminal for the multiplier.	-7.1V Error amp. output (3) EO
4	EI	I	Double function : reverse input terminal for error amp. The reference voltage inside the IC (2.5 VTYP) is inputted to non- reverse input terminal.	EI (4)
5	OVP	I	Overvoltage detection terminal It is an input terminal with over- voltage detection function which can detect the overvoltage of the output voltage to shut off the power MOS FET.	Overvoltage

Pin No.	Pin name	I/O	Terminal description	Internal equivalent circuit
6	VB	Ι	Transformer reset detection terminal The terminal, which is connected through resistor with sub-winding of transformer, detects the reset of transformer to send trigger signal which turns on power MOS FET. Since the winding signal of trans- former is inputted as current, the IC incorporates the circuit which clamps the upper/lower limit voltage to prevent malfunction.	VB 6
7	GND	_	Ground terminal Double function : Ground termi- nal for control system and power system	GND (7) Power system GND Signal system GND
8	VOUT	0	Output terminal It can directly drive the gate of power MOS FET.	9 V _{cc} 9 V _{cc} 8 Vout
9	PV _{cc}	_	Supply voltage terminal : The sup- ply voltage terminal for the power system and that for the signal sys- tem are put together with wire to greatly decrease the common impe- dance. This double-functioning terminal monitors the supply voltage and has start/stop operation threshold.	V _{cc} 9 UVLO VB upper limit voltage clamp VB upper block

Operation Descriptions

1. Normal control

(1) Application outline

As shown in Fig.1, the standard application of the AN8032 is a booster chopper circuit, which inputs the voltage rectified from the commercial supply of 100/200V (A in Fig.1) and outputs the DC voltage of 400V (B in Fig.B).

It controls so that the input current proportional to the input voltage (C, D in Fig.1) could be flown.

The output voltage of 400V is selected, considering the withstand voltage of parts and the operation limitation of booster chopper (input voltage < output voltage) under the worldwide input voltage.



Fig.1 Application Outline

(2) Control Outline (Refer to Fig.2 and 3)

1) Input (Ein) detection

The voltage which is divided from the input voltage of chopper circuit (Ein) by using external resistor is inputted to the multiplier input terminal of the AN8032 (MPI terminal).

2) Output (Eout) detection

The voltage which is divided from the output voltage of chopper circuit (Eout) by using external resistor is amplified by the error amplifier of the AN8032 (non-reverse input terminal (EI terminal) for input to another multiplier input (EO terminal, which also functions as output for error amplifier).

3) Multiplication of input voltage and output one

The signals inputted to the multiplier is multiplied and outputted from the multiplier. This output is a signal which monitors both of the input voltage and output one of the chopper circuit.



Fig.2 Normal Control Operation

4) Switching device current

The voltage generated in the current detection resistor which is connected to the switching device (power MOS FET) is detected at the CS terminal. In addition, for the above resistor, low resistance is selected, considering the power dissipation.

5) Switching device turning-off

The CS terminal voltage and the multiplier output voltage are compared by the current detection comparator. When the former value gets larger than the latter one, the current detection comparator sends the reset signal to the RS latch circuit to turn off the switching device.

6) Output current supply

When the switching device is turned off, the current flowing in the transformer is cut off. The diode is energized with inertia current of inductor to supply current to the output of chopper circuit (Eout).



Fig.3 Block Diagram under Normal Operation

7) Transformer reset signal (VB) detection

When the excitation energy is discharged and the inertia current of the inductor is lost, the transformer starts resonance with the frequency which depends on incidental C value of the board or parts and "L" value of the inductor. This operation is detected by the VB terminal through sub-winding provided on the transformer.

8) Switching device turning-off

By resonance, the turning-on signal is sent to the switching device, timing with the operation that the voltage of the sub-winding fluctuates from "H" to "L."

9) Operation repetition

When the switching device is turned on, current flows in the inductor. Thus, the above operation is repeated.

(Summary)

- 1) When the excitation energy of transformer is lost and the free resonance is started, the switching device is turned on.
- The switching device is turned on, when the following two elements are crossed : the product of the input voltage (Ein) and output one (Eout) of the chopper circuit and the switching device current.
- The fluctuation of input voltage and load current is controlled by changing the peak value height of switching device current.
- 4) The purpose of mixing two signals by using the multiplier :
 - 1) To stabilize the control system
- 2) To reduce the number of parts required

(3) Description of each function

VB

Function

It detects the discharge of the excitation energy of the inductor (reset operation) and turns on the power MOS FET at the next cycle.

Method used

When the inductor is reset, the sub-winding provided on the inductor (bias winding) starts free resonance. It is difficult from the view of withstand voltage to input this voltage directly to the IC. For this reason, it is inputted to the VB terminal through resistor.

Function of upper limit voltage clamper

It prevents the damage due to the voltage of VB terminal exceeding the withstand voltage.

Function of lower limit voltage clamper

It prevents the malfunction due to fluctuation to negative voltage of the VB terminal. (Generally, for the monolithic IC, malfunction such as latch-up is caused when the terminal voltage decreases under - VBE to activate the incidental device.

IC inside

The VB terminal voltage is inputted to the comparator with hysteresis inside the IC. For this reason, if the VB terminal voltage is under the threshold, the power MOS FET is turned on. However, it is preceded by the off-signal which is given to the power MOS FET by the overvoltage protective function, if any.



Fig.4 VB Terminal Outline



Fig.5 VB Operation

• Setting the VB terminal constant



Zero-cross switching

Zero-cross switching can be realized by using the partial resonance at turning-off of the power MOS FET, in order to suppress the dissipation.

The resonance capacitor CP is connected between the drain sources of the power MOS FET. After discharge of accumulation energy of the transformer, resonance with transformer inductance LP in the primary side is produced. Capacitor for delay is connected to the VB terminal so that the next turning-on could occur, timing with the operation that the resonance is produced and the drain voltage of the power MOS FET reaches around 0V. However, particular care should be taken, because zero-cross conditions could deviate from the theoretical ones since the delay amount fluctuates with the conditions such as input voltage.



CS

MPI

This terminal detects the current when the power MOS FET is turned on.

The current which flows when the power MOS FET is turned on is equivalent with the current flowing in the inductor. Therefore, the necessary power value can be controlled by controlling the peak value of the above current.

The input D-range of this terminal is from 0 to 5V. However, since dissipation gets large when the resistance which detects the power MOS FET current is set large, 0.22 to 0.47Ω is recommended for the resistance value, considering relationship with the S/N. The charging/discharging current for the incidental capacitance which is provided in the power MOS FET, transformer or printed wiring, flows in the power MOS FET detection resistor. This generates noise and may cause malfunction. Therefore, filter should be incorporated to remove such irregular element.



Fig.6 Pin descriptions of CS

This terminal monitors the AC input voltage. It inputs the voltage which is resistance-divided from the input voltage after fullwave rectification. Input D-range of the multiplier is from 0 to 4.5VTYP and output one is from 0 to 5.4VTYP.

EI/EO

The EI receives input after resistance division of output voltage of the active filter.

The EI is a reverse input for error amplifier. The reference voltage (2.5VTYP) temperature-compensated is inputted to the non-reverse input.

The error amplifier amplifies the error amount between the output voltage and the reference voltage for output to the multiplier. Resistor connected between the EI and EO determines the gain of error amplifier.

Resistance divider decreases the output voltage of the active filter to the input D-range of the EI. If small-sized resistor is used for it to suppress the dissipation, resistance value becomes high because of its high output voltage.

For this reason, particular care should be taken : if the capacitance for phase compensation inserted between the EI and EO is large, the delay element between it and the resistance divider of high resistance becomes large, adversely affecting the characteristics (overshoot or undershoot) at dramatic change of load,

Therefore, the value of the phase compensation capacitance should be set minimum to prevent the oscillation.



Fig.7 EI/EO Terminal Outline

VOUT

For the drive circuit, the AN8032 employs the totem pole type by which the power MOS FET can be directly driven. Since the peak output current is $\pm 1A$, the power MOS FET of TO-220 class can be driven. For the TOP-3 class, the buffer circuit should be added outside because its capability is not sufficient for that class.

The power MOS FET momentarily fluctuates to minus due to incidental capacitance between the drain gates at turning-off. And it may cause malfunction. Therefore, the shottkey diode should be inserted between the VOUT and GND, if necessary.



Fig.8 VOUT Terminal Outline



For the AN8032, the following method is used to suppress the interference between the two power supply lines : The supply voltage supply line of the power system and that for the signal line are separately provided in the IC chip and they are put together when wiring to the pin of the package.

The same method is also used for the GND line.

However, the above method can prevent all the malfunctions due to noise. For the route in which the drive current of the power MOS FET flows, the pattern wiring should be provided as short as possible, in the same way as conventional practice, to suppress the invasion of nose of the drive system.



2. Protective circuit

(1) Timer

For control of the AN8032, the chopper circuit can not start unless the switching device receives the first ON. And, the chopper circuit can not re-start, if the turning-on timing of switching device is missed due to some abnormality.

For this reason, the AN8032 incorporates the timer circuit, with which the start pulse is generated once for approx. 400µs (typ.) when the chopper circuit stops. So, any special external parts are not required (Refer to Fig.9).

However, in order to prevent the output rise of the chopper circuit, the timer circuit does not operate while the overvoltage protector is operating.



Fig.9 Timer Operation

(2) Overvoltage protection

1) Causes of overvoltage

In the booster chopper circuit, control is made so that the input power could become zero when the load current reaches zero. However, in the actual condition the input power can not be decreased to zero and the output voltage should rise, leaving control.

The above out-of-control condition is created as follows : The operation of the switching device can not be controlled for stop during delay time which exists between the turning-on to the turning-off of the switching device (Refer to Fig.10).

In order to prevent such problem, the AN8032 incorporates the overvoltage protective circuit and the necessary external parts can be much decreased.



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2) Overvoltage protector operation

For the AN8032, the input of the error amplifier which detects the output voltage is provided separately from the input of the overvoltage protective comparator. It is different at this point from the AN8031.

The settings are shown in the following :

- $\cdot\,$ Control reference voltage of the error amplifier : 2.50V (typ.)
- · Detection voltage of the overvoltage comparator : 2.63V (typ.) <Without hysteresis>
- (Voltage 5% higher than the control reference voltage of the error amplifier)

When the output voltage becomes high by 5% or more, comparing with the normal control voltage, the overvoltage comparator operates to cut off the switching device.

When overvoltage is detected, the timer circuit is cut off. It prevents the operation of power MOS FET which increases the output voltage further.

Therefore, under no load, the output voltage of the chopper circuit is stabilized at the value which is 5% higher than the normal control voltage and does not exceed that value (Refer to Fig.11).

In addition, the increase/decrease of the output voltage is created by the offset amount of the overvoltage comparator.



Fig. 11 Overvoltage Protection Operation

3) Output voltage overshoot at start

At operation start, the output overload condition is created because the smoothing capacitor which is connected to the output is charged. Under this condition the chopper circuit operates with full power. However, it does not immediately come out of the full-power-operation due to control delay of the entire feedback system even when the proper output voltage is obtained, causing the overshoot of output voltage. The AN8032 overvoltage protector operates even at operation starts and prevents the worst cases such as damage of used parts (Refer to Fig.12).



Fig.12 Output Voltage Overshoot at Operation Start

• Differences between the AN8031 and the AN8032

AN8031 : EI terminal as the output voltage monitor function and the overvoltage detective function

AN8032 : The above two functions are separately provided (VCC terminal both for PVCC and VCC)

EI terminal ; Only for output voltage monitor

OVP terminal ; Only for overvoltage detection

Reason for model change

The AN8031 can not suppress the overvoltage generated between the pins of the active filter output voltage monitor resistor during the short test.



Countermeasures taken in AN8032

The output voltage monitor system and the overvoltage detective system are separately provided.



Note) The OVP terminal is located at the side of EI terminal, considering the board pattern design.

Application Circuit





■ Start Waveform (20ms/div)



■ Stop Waveform (20ms/div)



